

# 低消費電力SRAM 発注型名

**R1 L V 5256 E SA - 5 S I #B1**

**R1 L P 04 08 D SP - 5 S I #B1**

**RM L V 04 16 E G SB - 4 S 2 #A A 1**

RENESAS Memory

Chip configuration

<b>L</b>	LPSRAM, Single chip
<b>W</b>	LPSRAM, Two chips

Operating Voltage

<b>V</b>	3V
<b>P</b>	5V

Memory Density

<b>5256</b>	256Kb (x8)
<b>01</b>	1Mb
<b>02</b>	2Mb
<b>04</b>	4Mb
<b>08</b>	8Mb
<b>16</b>	16Mb
<b>32</b>	32Mb
<b>64</b>	64Mb

Bus Width

<b>08</b>	x8
<b>16</b>	x16

Chip Generation

Industrial Grade

Package Type

<b>SA</b>	TSOP-I (256Kb/8Mb/16Mb/32Mb/64Mb) sTSOP (1Mb/2Mb/4Mb)
<b>SB</b>	TSOP-II
<b>SD</b>	μTSOP
<b>SF</b>	TSOP-I (1Mb)
<b>SP</b>	SOP (256Kb, 4Mb)
<b>SN</b>	SOP (1Mb)
<b>BG</b>	FBGA

Packing, Environmental

	Packing	Environmental
<b>#B0 / #B1</b>	Tray or Magazine	Pb free
<b>#S0 / #S1</b>	Tape & Reel	Pb free

Assembly Site Rev. , etc.

<b>0</b>	Rev. Code
<b>1</b>	Rev. Code

Environment

<b>A</b>	Pb free (pure-Tin plating)
<b>C</b>	Pb free (non pure-Tin plating)

Packing

<b>A</b>	Tray
<b>C</b>	Magazine
<b>H</b>	Tape & Reel (TSOP-II, uTSOP, SOP)
<b>K</b>	Tape & Reel (FBGA, TSOP-I, sTSOP)

Operating Temperature

<b>R</b>	0 to 70 deg. C
<b>I</b>	-40 to 85 deg. C
<b>2</b>	-40 to 85 deg. C

Access time

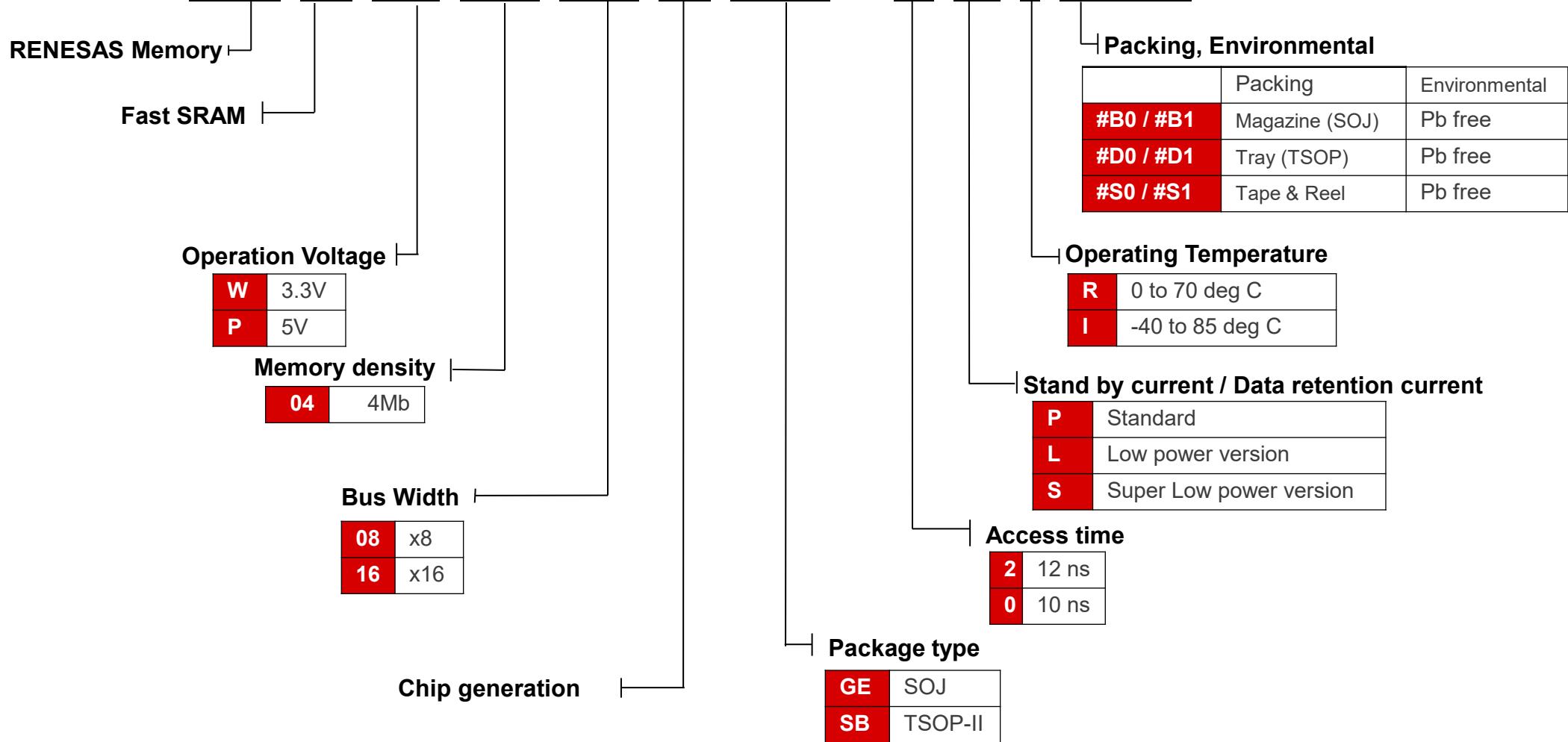
<b>5</b>	55 ns
<b>4</b>	45 ns

Stand-by current / Data retention current

<b>S</b>	Low power version
<b>U</b>	Ultra Low power version

# 高速 4Mb SRAM 発注型名

## R1 R W 04 16 D SB - 2 P I #D1



Example shown here: Part number R1RW0416DSB-2PI#D1